ON Semiconductor

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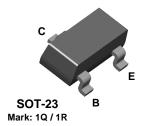


ON Semiconductor®

2N5088 2N5089

MMBT5088 MMBT5089





NPN General Purpose Amplifier

This device is designed for low noise, high gain, general purpose amplifier applications at collector currents from $1\mu A$ to 50 mA.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter		Value	Units
V_{CEO}	Collector-Emitter Voltage	2N5088	30	V
		2N5089	25	V
V_{CBO}	Collector-Base Voltage	2N5088	35	V
		2N5089	30	V
V_{EBO}	Emitter-Base Voltage		4.5	V
Ic	Collector Current - Continuous		100	mA
T _J , T _{sta}	Operating and Storage Junction Temperature Range		-55 to +150	°C

 $^{{}^{\}textstyle \star} \text{These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.}$

NOTES

1) These ratings are based on a maximum junction temperature of 150 degrees C.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units
		2N5088 2N5089	*MMBT5088 *MMBT5089	
P _D	Total Device Dissipation	625	350	mW
	Derate above 25°C	5.0	2.8	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	°C/W

^{*}Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

²⁾ These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

450

300

400

0.5

0.8

٧

٧

5089

5088

5089

(continued)

Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions		Min	Max	Units
OFF CHAP	RACTERISTICS					
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	5088 5089	30 25		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 100 \ \mu\text{A}, \ I_E = 0$	5088 5089	35 30		V V
I _{CBO}	Collector Cutoff Current	V _{CB} = 20 V, I _E = 0 V _{CB} = 15 V, I _E = 0	5088 5089		50 50	nA nA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 3.0 V, I _C = 0 V _{EB} = 4.5 V, I _C = 0			50 100	nA nA
ON CHAR	ACTERISTICS					
h _{FE}	DC Current Gain	$I_C = 100 \mu A, V_{CE} = 5.0 \text{ V}$ $I_C = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V}$	5088 5089 5088	300 400 350	900 1200	

 $I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}^*$

 $I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$

 $I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$

SMALL SIGNAL CHARACTERISTICS

Base-Emitter On Voltage

Collector-Emitter Saturation Voltage

f _T	Current Gain - Bandwidth Product	$I_C = 500 \mu\text{A}, V_{CE} = 5.0 \text{mA},$ $f = 20 \text{MHz}$	50		MHz
C _{cb}	Collector-Base Capacitance	$V_{CB} = 5.0 \text{ V}, I_E = 0, f = 100 \text{ kHz}$		4.0	pF
C _{eb}	Emitter-Base Capacitance	$V_{BE} = 0.5 \text{ V}, I_{C} = 0, f = 100 \text{ kHz}$		10	pF
h _{fe}	Small-Signal Current Gain	I _C = 1.0 mA, V _{CE} = 5.0 V, 5088 f = 1.0 kHz 5089	350 450	1400 1800	
NF	Noise Figure	$I_C = 100 \ \mu A, \ V_{CE} = 5.0 \ V, \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ $		3.0 2.0	dB dB

^{*}Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

Spice Model

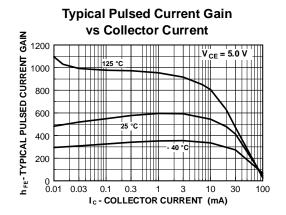
 $V_{CE(sat)}$

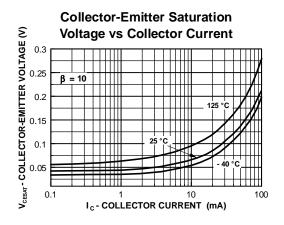
 $V_{BE(on)}$

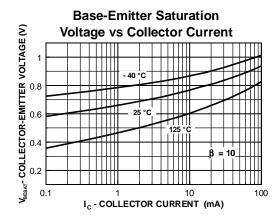
 $NPN \ (Is=5.911f \ Xti=3 \ Eg=1.11 \ Vaf=62.37 \ Bf=1.122K \ Ne=1.394 \ Is==5.911f \ Ikf=14.92m \ Xtb=1.5 \ Br=1.271 \ Nc=2 \ Isc=0 \ Ikr=0 \ Rc=1.61 \ Cjc=4.017p \ Mjc=.3174 \ Vjc=.75 \ Fc=.5 \ Cje=4.973p \ Mje=.4146 \ Vje=.75 \ Tr=4.673n \ Tf=821.7p \ Itf=.35 \ Vtf=4 \ Xtf=7 \ Rb=10)$

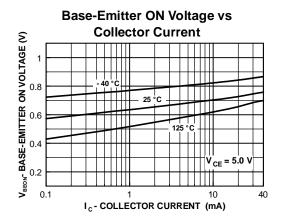
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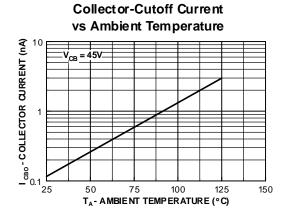
Typical Characteristics







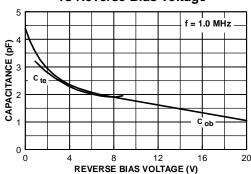




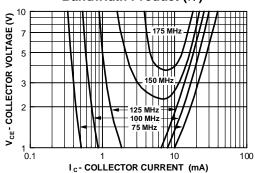
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Typical Characteristics (continued)

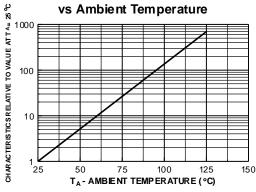
Input and Output Capacitance vs Reverse Bias Voltage



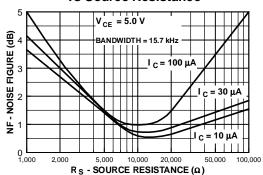
Contours of Constant Gain Bandwidth Product (f_T)



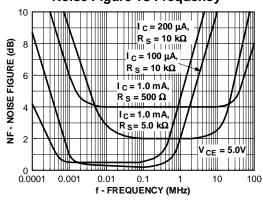
Normalized Collector-Cutoff Current vs Ambient Temperature



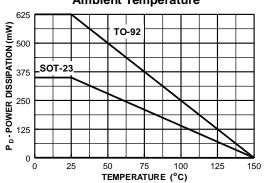
Wideband Noise Frequency vs Source Resistance



Noise Figure vs Frequency



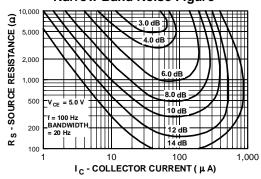
Power Dissipation vs Ambient Temperature



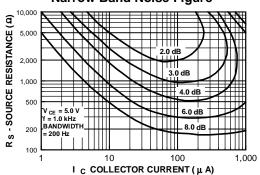
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Typical Characteristics (continued)

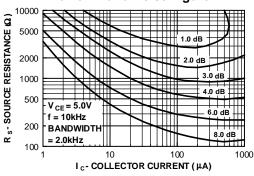
Contours of Constant Narrow Band Noise Figure



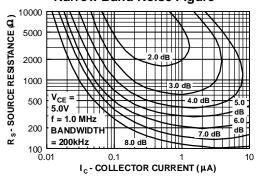
Contours of Constant Narrow Band Noise Figure



Contours of Constant Narrow Band Noise Figure



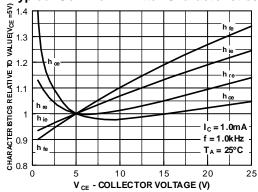
Contours of Constant Narrow Band Noise Figure



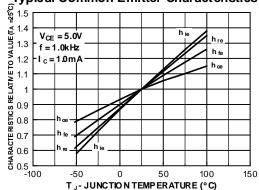
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Typical Common Emitter Characteristics (f = 1.0 kHz)

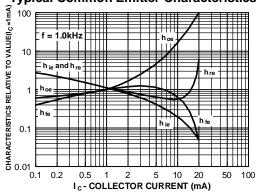
Typical Common Emitter Characteristics



Typical Common Emitter Characteristics



Typical Common Emitter Characteristics



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